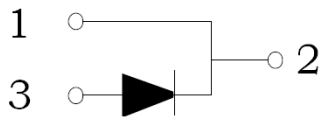


TO-220FAC

Ultrafast Recovery Diode in a TO-220FAC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode



PIN1 2 Cathode

PIN 3 Anode

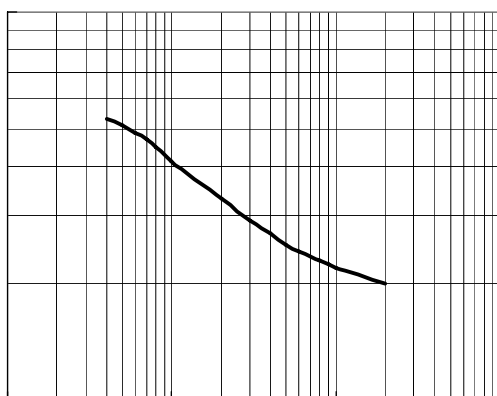
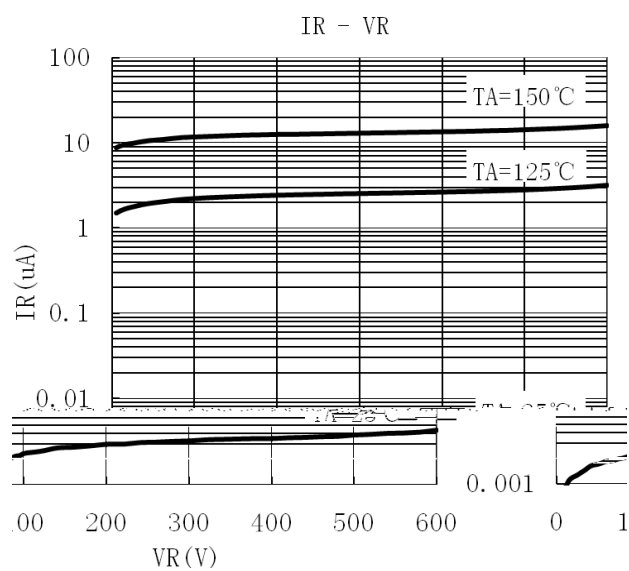
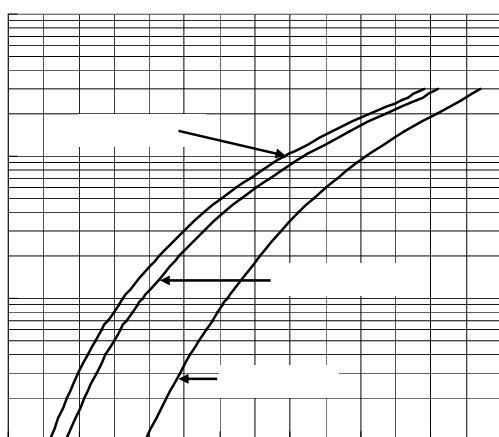
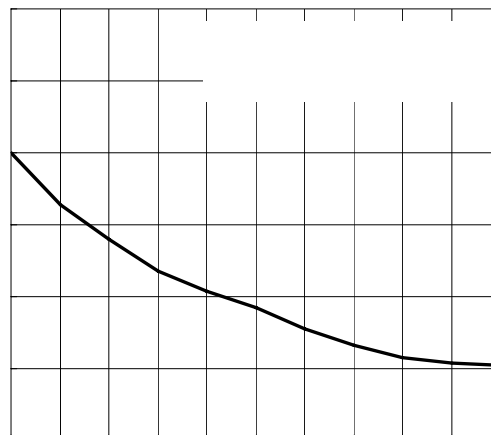
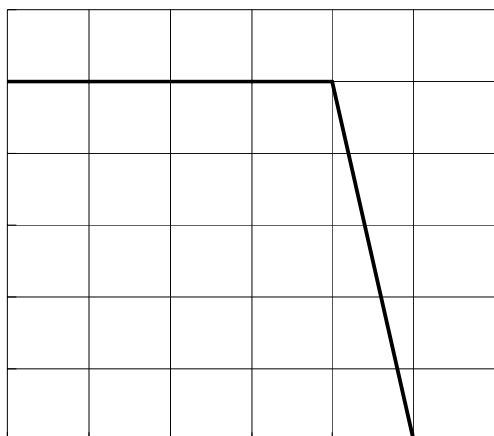
See Marking Instructions

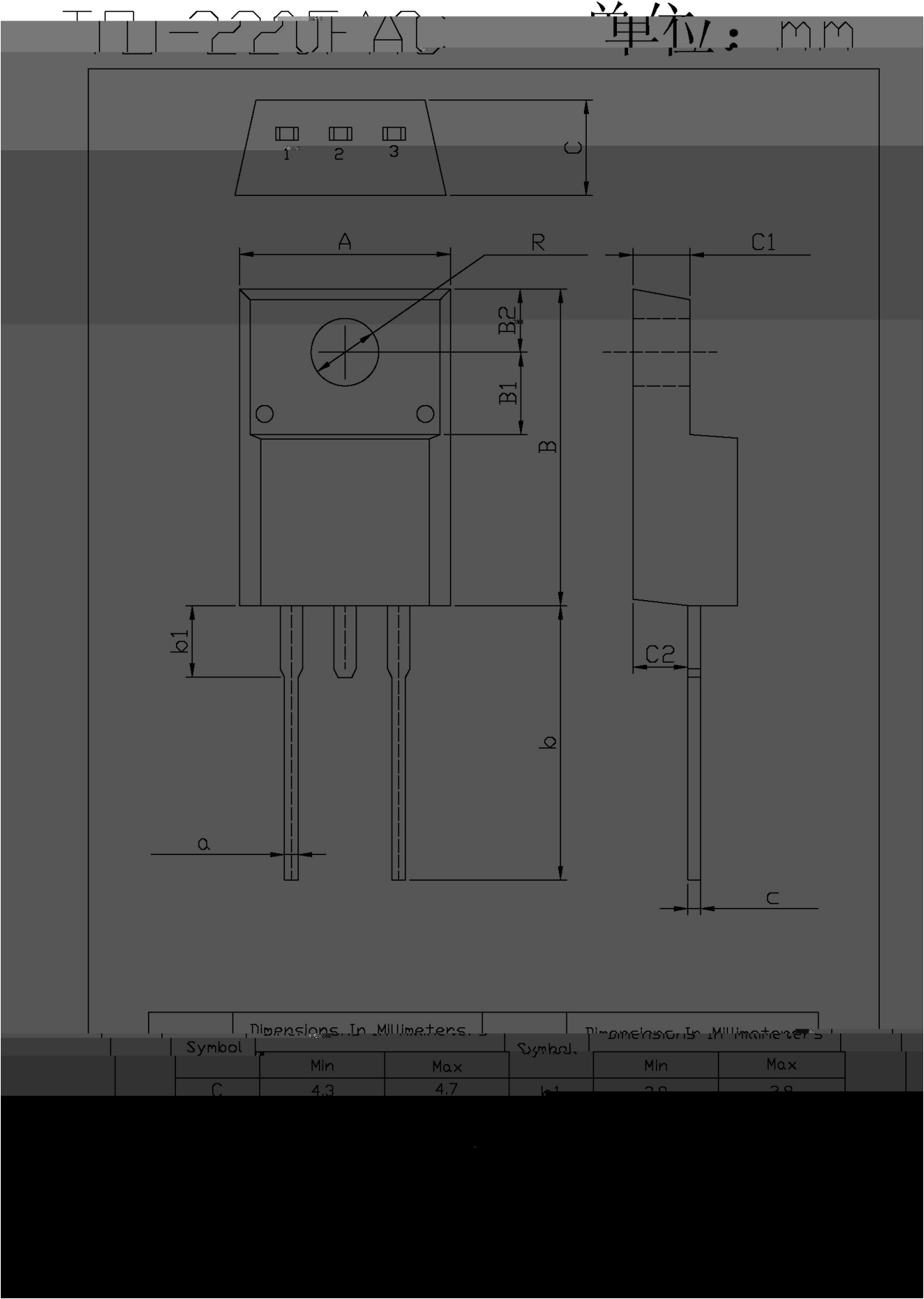
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Forward Current	I_F	1 10	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	4	/W
Junction Temperature Range	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

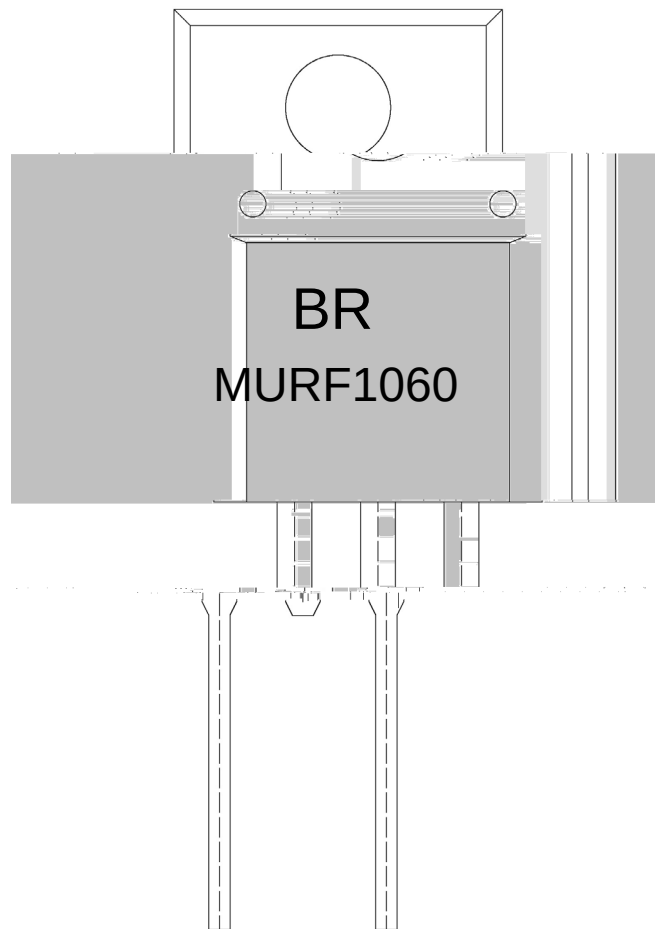
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	600			V
Forward Voltage	V_F	$I_F=2.0A$ $T_C=25$		1.0	1.2	V
		$I_F=2.0A$ $T_C=125$		0.80	1.0	
		$I_F=10A$ $T_C=25$		1.3	1.5	
		$I_F=10A$ $T_C=125$		1.2	1.4	
Instantaneous Reverse Current	I_R Note 1	$V_R=600V$ $T_a=25$			10	μA
		$V_R=600V$ $T_a=125$			500	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			50	ns

/Notes

1.







BR

MURF1060

Note:

BR:

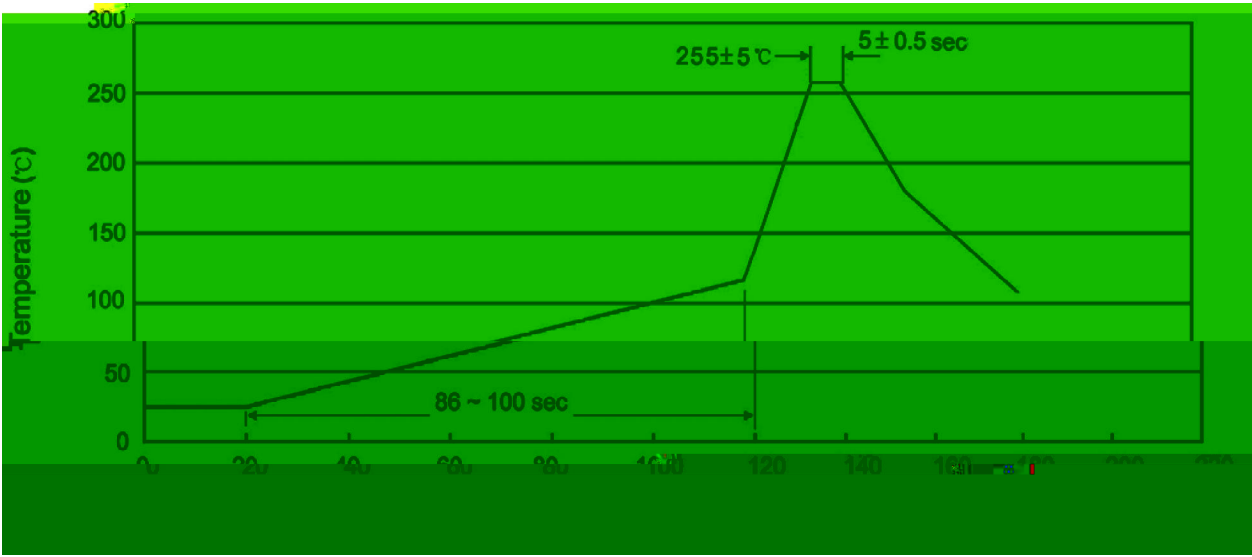
Company Code

MURF1060

Product Type.

****:

Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只套管	套管盒	只盒	盒箱	只箱	套管	盒	箱